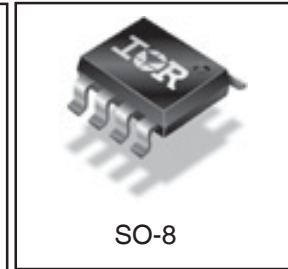
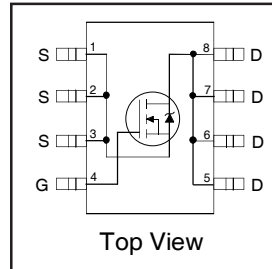


HEXFET® Power MOSFET

$V_{DS}$	<b>20</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = 4.5V$ )	<b>0.022</b>	$\Omega$
$Q_g$	<b>48</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>8.7</b>	<b>A</b>



**Features**

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification

⇒

**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7401PbF-1	SO-8	Tube/Bulk	95	IRF7401PbF-1
		Tape and Reel	4000	IRF7401TRPbF-1

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	10 Sec. Pulsed Drain Current, $V_{GS} @ 4.5V$	10	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	8.7	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	7.0	
$I_{DM}$	Pulsed Drain Current ①	35	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

**Thermal Resistance Ratings**

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	—	50	°C/W

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

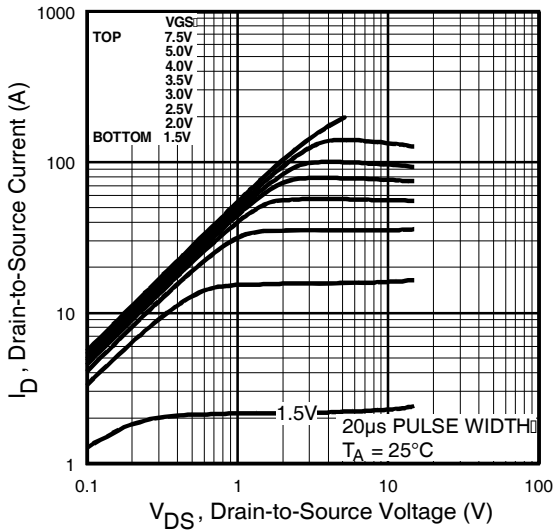
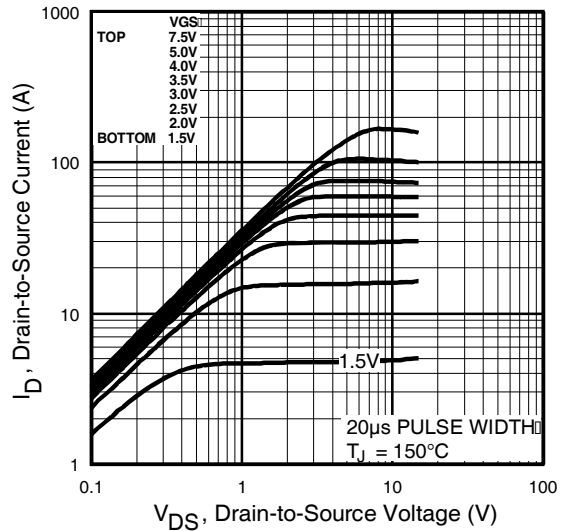
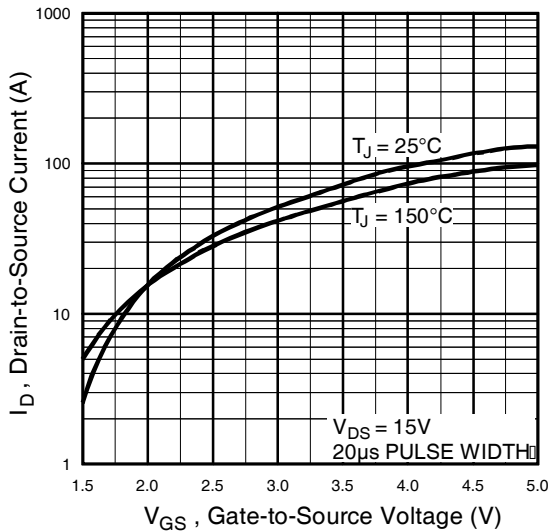
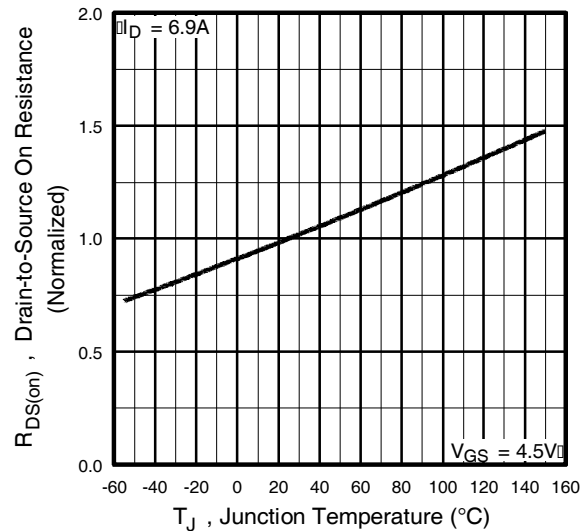
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.044	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance	—	—	0.022	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.1A ③
		—	—	0.030		V <sub>GS</sub> = 2.7V, I <sub>D</sub> = 3.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.70	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	11	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4.1A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125 °C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -12V
Q <sub>g</sub>	Total Gate Charge	—	—	48	nC	I <sub>D</sub> = 4.1A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	5.1		V <sub>DS</sub> = 16V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	20		V <sub>GS</sub> = 4.5V, See Fig. 6 and 12 ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	—	ns	V <sub>DD</sub> = 10V
t <sub>r</sub>	Rise Time	—	72	—		I <sub>D</sub> = 4.1A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	65	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	92	—		R <sub>D</sub> = 2.4Ω, See Fig. 10 ③
L <sub>D</sub>	Internal Drain Inductance	—	2.5	—	nH	Between lead tip and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	4.0	—		
C <sub>iss</sub>	Input Capacitance	—	1600	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	690	—		V <sub>DS</sub> = 15V
C <sub>riss</sub>	Reverse Transfer Capacitance	—	310	—		f = 1.0MHz, See Fig. 5

**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	35		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 2.0A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	39	59	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 4.1A
Q <sub>rr</sub>	Reverse Recovery Charge	—	42	63	nC	di/dt = 100A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② I<sub>SD</sub> ≤ 4.1A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Surface mounted on FR-4 board, t ≤ 10sec.


**Fig 1.** Typical Output Characteristics

**Fig 2.** Typical Output Characteristics

**Fig 3.** Typical Transfer Characteristics

**Fig 4.** Normalized On-Resistance Vs. Temperature

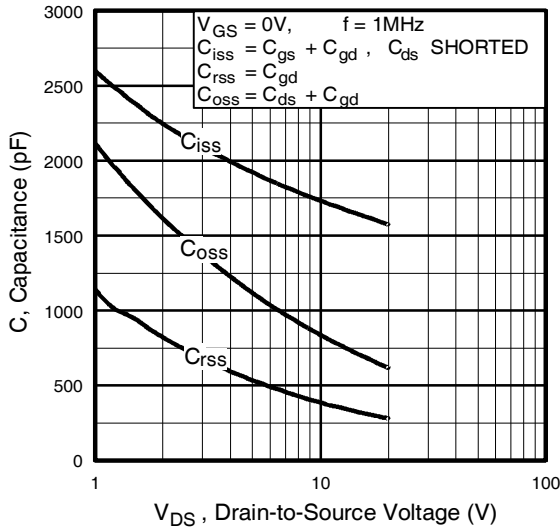


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

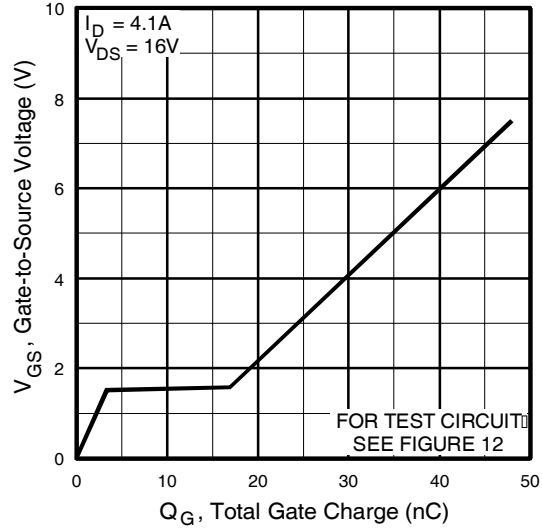


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

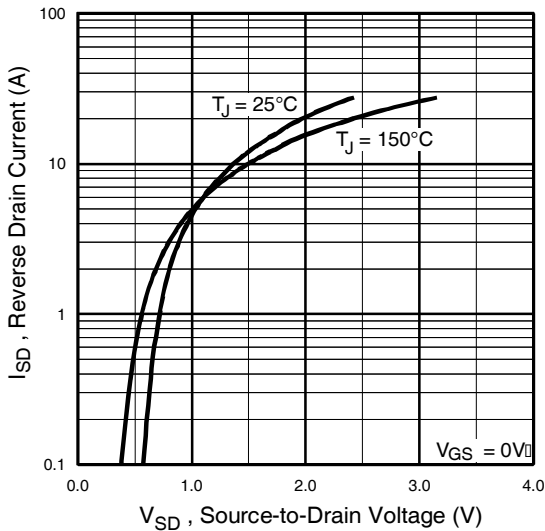


Fig 7. Typical Source-Drain Diode Forward Voltage

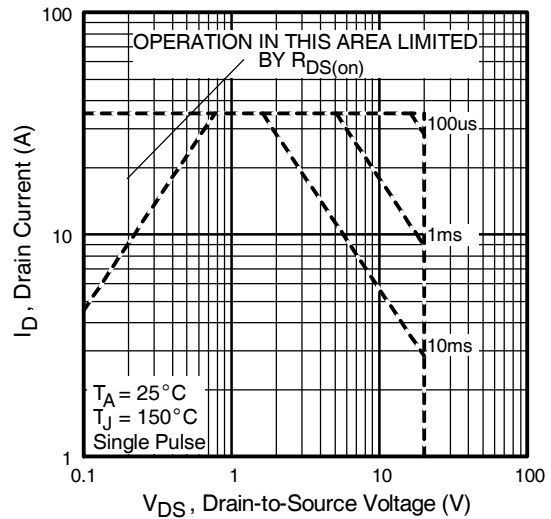
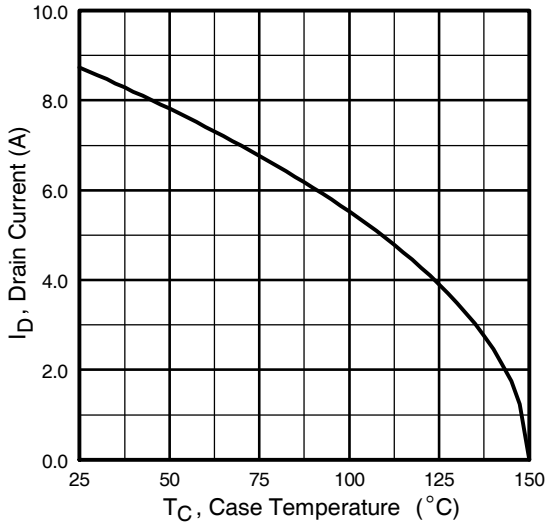
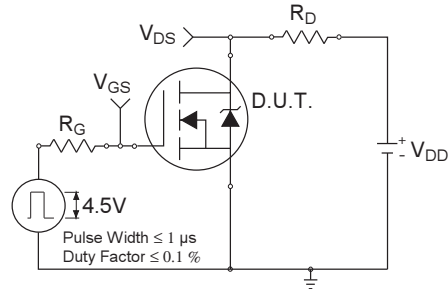


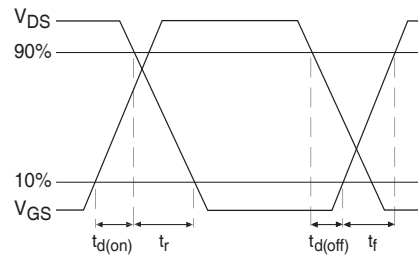
Fig 8. Maximum Safe Operating Area



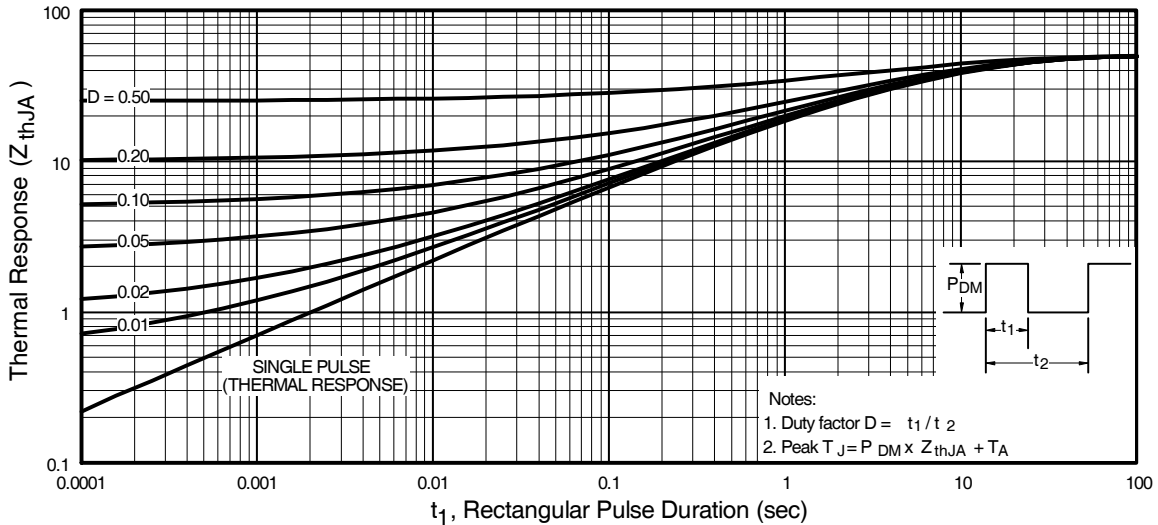
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

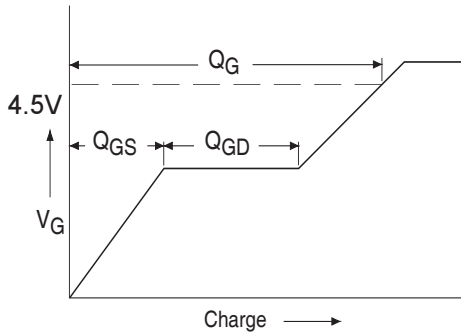


Fig 12a. Basic Gate Charge Waveform

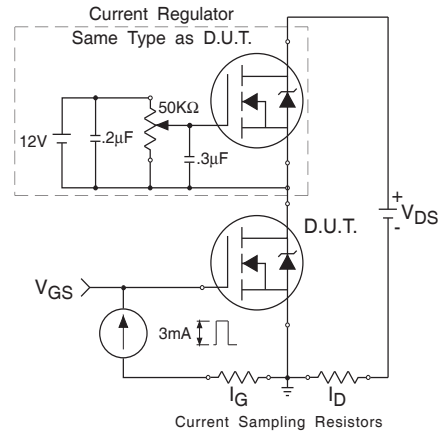
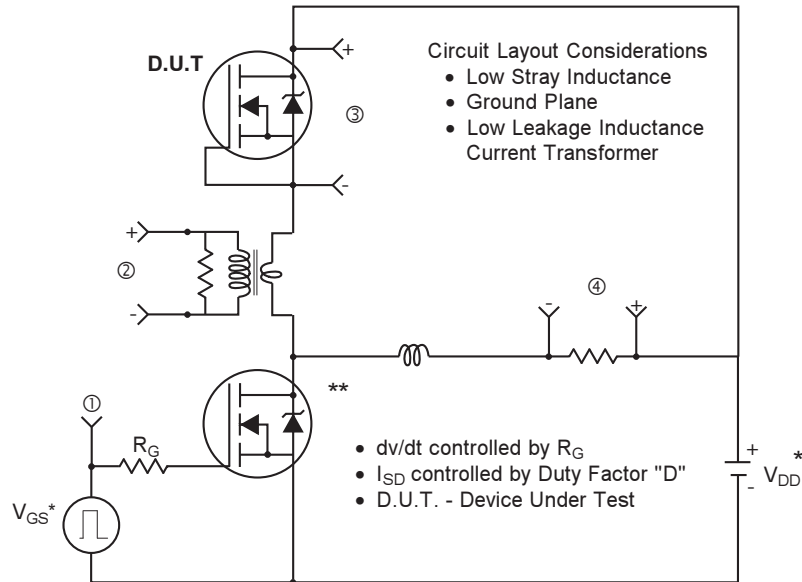
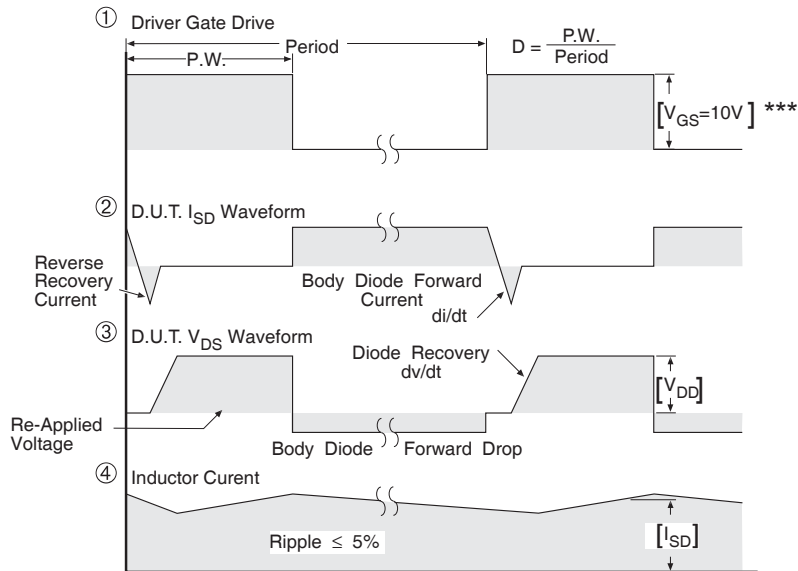


Fig 12b. Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**


\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements

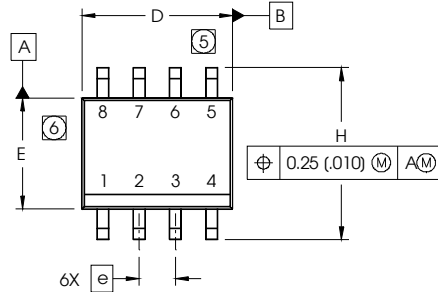


\*\*\*  $V_{GS} = 5.0V$  for Logic Level and  $3V$  Drive Devices

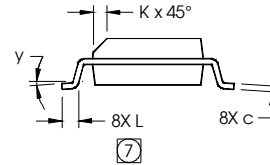
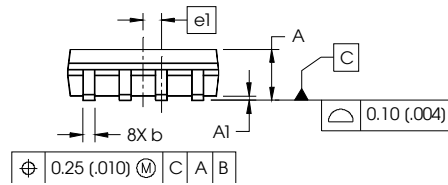
**Fig 13. For N-Channel HEXFETS**

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



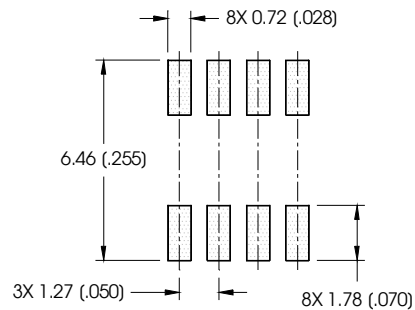
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

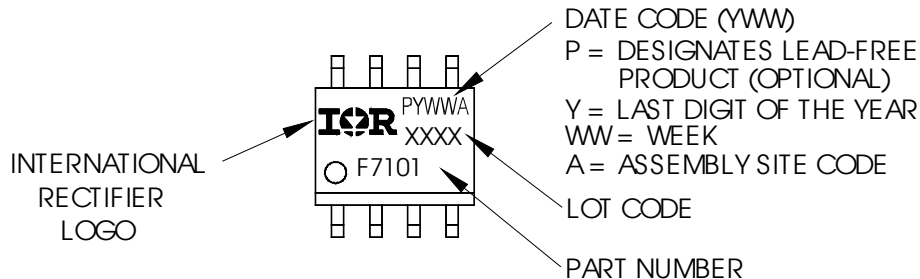
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



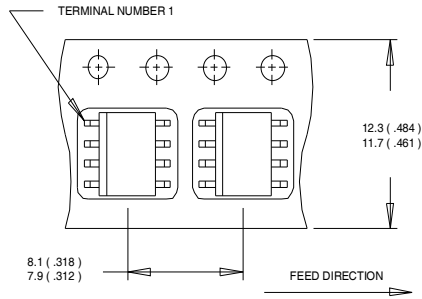
## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

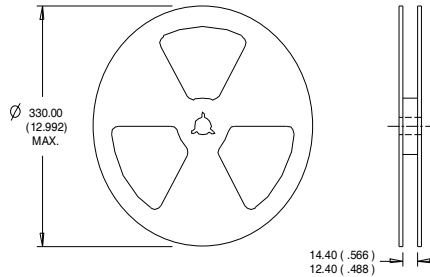


Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



**SO-8 Tape and Reel** (Dimensions are shown in millimeters (inches))


- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**Qualification information<sup>†</sup>**

Qualification level	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release